

Contents

Chapter 1: Introduction	1
1.1 Power Amplifier Design and System Requirements.....	2
1.2 Partitioning Design Approach.....	3
1.3 Dissertation Organization	5
Chapter 2: AlGa_N/Ga_N-HEMTs	8
2.1 Ga _N Semiconductor Material	8
2.1.1 Ga _N -HEMT Structure.....	10
2.1.2 Trapping Effect and Performance Limit in Ga _N -HEMTs	12
2.2 Device Modeling Approach	14
Chapter 3: Efficiency and Linearity Enhancement Techniques in Power Amplifiers	16
3.1 Nonlinearity and Memory-Effects	17
3.1.1 Harmonics, AM/AM- and AM/PM-Conversion.....	17
3.1.2 Intermodulation Distortion	18
3.1.3 Adjacent Channel Power Ratio	20
3.1.4 Memory-Effects	21
3.2 Single-Stage Amplifier Operation Modes.....	22
3.2.1 CW Mode Amplifiers	23
3.2.2 Harmonic Tuning Techniques	27
3.3 Doherty Efficiency Enhancement Technique	28
3.3.1 Doherty Power Amplifier	28
3.3.1.1 Doherty Operation	30
3.3.1.2 Linearity of Doherty Power Amplifier	35
3.3.2 Advanced Doherty Architecture	36
3.3.2.1 N-Way Doherty Power Amplifier	36
3.3.2.2 Multi-Stage Doherty Power Amplifier	37
Chapter 4: Characterization and Modeling of a 2-mm ALGa_N/Ga_N-HEMT	41
4.1 Small-Signal Modeling	41
4.1.1 Extrinsic Parameters Extraction.....	42
4.1.2 Intrinsic Parameters Extraction.....	46
4.2 Large-Signal Modeling	49

4.2.1	Gate Current and Charge Model	50
4.2.2	Drain Current Model	51
4.2.3	Small- and Large-Signal Model Verification.....	55
4.2.3.1	Small-Signal Verification	55
4.2.3.2	Pulsed-IV Characteristics.....	56
4.2.3.3	Output Power and Efficiency.....	56
4.2.3.4	Intermodulation Distortion Prediction	57
Chapter 5: Small-Signal In-Fixture Measurement for Microwave Integrated Sub-		
Circuits		59
5.1	In-Fixture Measurement	59
5.1.1	Extracting S-Parameters of each Fixture-half using T-Parameters Conversion.....	60
5.1.2	Extracting S-Parameters of each Fixture-half by Modeling their Characteristics	64
5.1.2.1	Modeling of the Two Cascaded Fixture-halves with Soldering Interconnection.....	66
5.1.2.2	Modeling of the Two Cascaded Fixture-halves with Bond Wire Interconnection.....	70
5.2	Characterization of Passive SMDs	73
5.2.1	SMD Inductor.....	74
5.2.2	SMD Capacitor.....	75
5.2.3	SMD Resistor	76
Chapter 6: Single-Stage Power Amplifier Design with a 2-mm GaN-HEMT Device		
.....		78
6.1	Micro-Packaged Device Characterization.....	79
6.2	Class-AB 2 W GaN-HEMT Power Amplifier Design	86
6.2.1	Bias Network Design	86
6.2.1.1	Drain Bias Network	87
6.2.1.2	Gate Bias Network.....	91
6.2.2	Matching Network Design	94
6.2.2.1	Optimum Impedance Determination.....	94
6.2.2.2	Input Matching Network Design	96
6.2.2.3	Output Matching Network Design.....	100
6.2.3	Power Amplifier Measurement Results	105
6.2.3.1	Small-Signal Performance	105
6.2.3.2	Large-Signal Performance	106

Chapter 7: Three-Way Doherty Power Amplifier Design.....	110
7.1 Standard Three-Way Doherty Power Amplifier Operation	110
7.2 Three-Way Doherty Power Amplifier with New Combiner.....	114
7.3 Design and Fabrication of a Three-Way Doherty Power Amplifier with the Proposed Combiner.....	117
7.3.1 Main and Peaking Amplifiers Design.....	117
7.3.2 Power Divider Design.....	120
7.3.2.1 Design of a Compact Wilkinson Power Divider	120
7.3.2.2 Divider Fabrication and Measurement	121
7.3.3 Power Combiner Design.....	125
7.3.4 Three-Way Doherty Power Amplifier Performance Evaluation	129
7.3.4.1 Small-Signal Performance.....	130
7.3.4.2 Large-Signal Performance.....	130
Chapter 8: Conclusions and Further Work	136
8.1 Conclusions from the Research Results.....	136
8.2 Outlook to Future Research	139
Appendices	140
A. Designed Doherty Power Amplifier	140
B. X-Parameters Measurement.....	142
C. Technical Laboratory.	144
C.1 LPKF Laser Machine	144
C.2 LPKF Drilling and Milling Machine.....	145
D. Bonding Machine.....	146
E. Comparison of On-Wafer Measured S-Parameters of Six Samples of the 2-mm GaN-HEMT Device	147
F. Schematic Diagrams of the Three-Way DPA	150
References	156